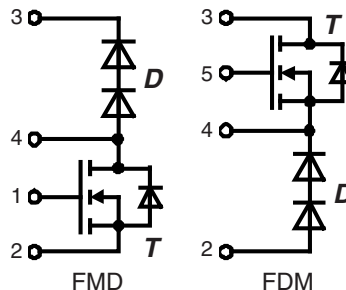


CoolMOS™ 1) Power MOSFET

with HiPerDyn™ FRED

Buck and Boost Topologies

Electrically isolated back surface
 2500 V electrical isolation
 N-Channel Enhancement Mode
 Low $R_{DS(on)}$, high V_{DSS} MOSFET
 Ultra low gate charge

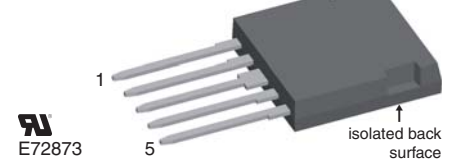


$$I_{D25} = 47 \text{ A}$$

$$V_{DSS} = 600 \text{ V}$$

$$R_{DS(on) \text{ max}} = 0.045 \Omega$$

ISOPLUS i4™



MOSFET T		Maximum Ratings	
Symbol	Conditions		
V_{DSS}	$T_{VJ} = 25^\circ\text{C}$	600	V
V_{GS}		± 20	V
I_{D25}	$T_C = 25^\circ\text{C}$	47	A
I_{D90}	$T_C = 90^\circ\text{C}$	32	A
E_{AS} E_{AR}	single pulse repetitive } $I_D = 11 \text{ A}; T_C = 25^\circ\text{C}$	1950 3	mJ mJ
dV/dt	MOSFET dV/dt ruggedness $V_{DS} = 0 \dots 480 \text{ V}$	50	V/ns

Features

- Silicon chip on Direct-Copper-Bond substrate
 - high power dissipation
 - isolated mounting surface
 - 2500 V electrical isolation
 - low drain to tab capacitance ($< 40 \text{ pF}$)
- Fast CoolMOS™ 1) power MOSFET 4th generation
 - high blocking capability
 - lowest resistance
 - avalanche rated for unclamped inductive switching (UIS)
 - low thermal resistance due to reduced chip thickness
- Enhanced total power density
- HiPerDyn™ FRED
 - consisting of series connected diodes
 - enhanced dynamic behaviour for high frequency operation

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}; I_D = 44 \text{ A}$		40	45	m Ω
$V_{GS(th)}$	$V_{DS} = V_{GS}; I_D = 3 \text{ mA}$	2.5	3	3.5	V
I_{DSS}	$V_{DS} = V_{DSS}; V_{GS} = 0 \text{ V}$			10	μA
				50	μA
I_{GSS}	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$			100	nA
C_{iss} C_{oss}	$V_{GS} = 0 \text{ V}; V_{DS} = 100 \text{ V}$ $f = 1 \text{ MHz}$		6800 320		pF pF
Q_g Q_{gs} Q_{gd}	$V_{GS} = 0 \text{ to } 10 \text{ V}; V_{DS} = 400 \text{ V}; I_D = 44 \text{ A}$		150 35 50	190	nC nC nC
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off} $E_{rec off}$	$V_{GS} = 10 \text{ V}; V_{DS} = 400 \text{ V}$ $I_D = 44 \text{ A}; R_G = 3.3 \Omega$		30 20 100 10		ns ns ns ns
			tbd		mJ mJ mJ
R_{thJC} R_{thCH}	with heat transfer paste		0.25	0.45	K/W K/W

$(T_{VJ} = 25^\circ\text{C}, \text{ unless otherwise specified})$

Applications

- Switched mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)
- Power factor correction (PFC)

Advantages

- Easy assembly: no screws or isolation foils required
- Space savings
- High power density
- High reliability

¹⁾ CoolMOS™ is a trademark of Infineon Technologies AG.

MOSFET T Source-Drain Diode

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)					
I_S	$V_{GS} = 0\text{ V}$			44	A
V_{SD}	$I_F = 44\text{ A}; V_{GS} = 0\text{ V}$		0.9	1.2	V
t_{rr}	$I_F = 44\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s}; V_R = 400\text{ V}$		600		ns
Q_{RM}			17		μC
I_{RM}			60		A

Diode D (data for series connection)

Symbol	Conditions	Maximum Ratings	
V_{RRM}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600	V
I_{F25}	$T_C = 25^{\circ}\text{C}$	95	A
I_{F90}	$T_C = 90^{\circ}\text{C}$	56	A

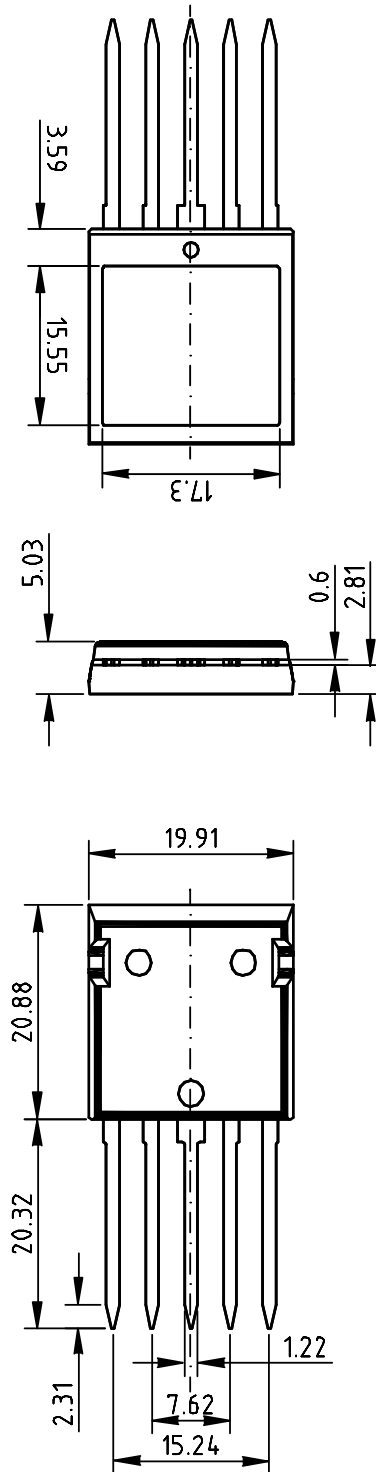
Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
V_F	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$		2.48	V
				3.02	V
	$I_F = 60\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$		1.89	A
				2.45	A
I_R	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$		1	μA
		$T_{VJ} = 150^{\circ}\text{C}$		0.2	mA
I_{FSM}	$t = 10\text{ ms (50 Hz), sine};$	$T_{VJ} = 45^{\circ}\text{C}$		450	A
I_{RM}	$I_F = 30\text{ A}; V_R = 100\text{ V};$ $-di_F/dt = 200\text{ A}/\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$		2	A
t_{rr}				30	ns
R_{thJC}	with heat transfer paste		0.25	0.55	K/W
R_{thCH}					K/W

Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}	operating	-55...+150	$^{\circ}\text{C}$
T_{stg}	storage	-55...+125	$^{\circ}\text{C}$
V_{ISOL}	$I_{ISOL} < 1\text{ mA}; 50/60\text{ Hz}$	2500	V~
F_C	mounting force with clip	20...120	N

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
C_P	coupling capacity between shorted pins and mounting tab in the case		40		pF
d_S, d_A	pin - pin	1.7			mm
d_S, d_A	pin - backside metal	5.5			mm
Weight			9		g

ISOPLUS i4™ Outline



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [IXYS](#) manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [IRFD120](#) [JANTX2N5237](#) [FCA20N60_F109](#) [FDZ595PZ](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [TPCC8103,L1Q\(CM](#)
[MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [SSM6J414TU,LF\(T](#) [751625C](#) [BUK954R8-60E](#) [NTE6400](#) [SQJ402EP-](#)
[T1-GE3](#) [2SK2614\(TE16L1,Q\)](#) [2N7002KW-FAI](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [ECH8691-TL-W](#) [FCAB21350L1](#) [P85W28HP2F-](#)
[7071](#) [DMN1053UCP4-7](#) [NTE221](#) [NTE222](#) [NTE2384](#) [NTE2903](#) [NTE2941](#) [NTE2945](#) [NTE2946](#) [NTE2960](#) [NTE2967](#) [NTE2969](#) [NTE2976](#)
[NTE6400A](#) [NTE2910](#) [NTE2916](#) [NTE2956](#) [NTE2911](#) [DMN2080UCB4-7](#) [TK10A80W,S4X\(S](#) [SSM6P69NU,LF](#) [DMP22D4UFO-7B](#)
[DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)